

TOSHIBA**TC74AC373P/F/FW/FT**

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC74AC373P, TC74AC373F, TC74AC373FW, TC74AC373FT**OCTAL D-TYPE LATCH WITH 3-STATE OUTPUT**

The TC74AC373 is an advanced high speed CMOS OCTAL LATCH with 3-STATE OUTPUT fabricated with silicon gate and double-layer metal wiring C2MOS technology. It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

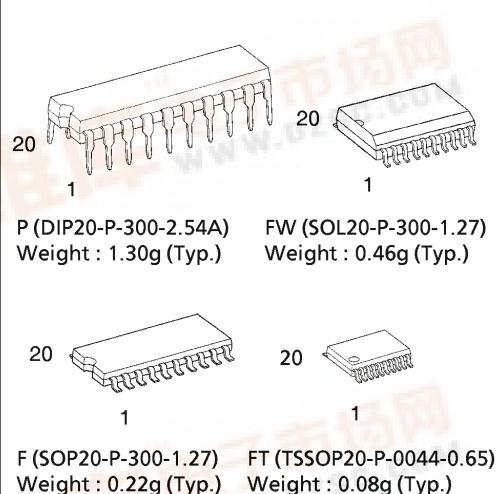
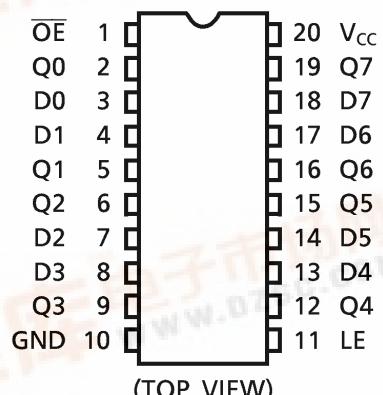
These 8-bit D-type latches are controlled by a latch enable input (LE) and a output enable input (\overline{OE}). When the \overline{OE} input is high, the eight outputs are in a high impedance state.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

FEATURES:

- High Speed..... $t_{pd} = 4.8\text{ns}(\text{typ.})$ at $V_{CC} = 5\text{V}$
- Low Power Dissipation..... $I_{CC} = 8\mu\text{A}(\text{Max.})$ at $T_a = 25^\circ\text{C}$
- High Noise Immunity..... $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (Min.)
- Symmetrical Output Impedance..... $|I_{OH}| = I_{OL} = 24\text{mA}(\text{Min.})$
Capability of driving 50Ω transmission lines.
- Balanced Propagation Delays..... $t_{PLH} \approx t_{PHL}$
- Wide Operating Voltage Range..... $V_{CC} (\text{opr}) = 2\text{V} \sim 5.5\text{V}$
- Pin and Function Compatible with 74F373

(Note) The JEDEC SOP (FW) is not available in Japan.

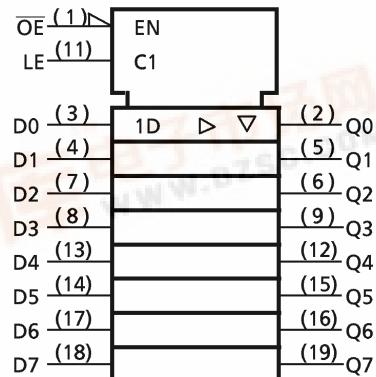
**PIN ASSIGNMENT****TRUTH TABLE**

INPUTS			OUTPUTS
\overline{OE}	LE	D	Q
H	X	X	Z
L	L	X	Q_n
L	H	L	L
L	H	H	H

X : Don't Care

Z : High Impedance

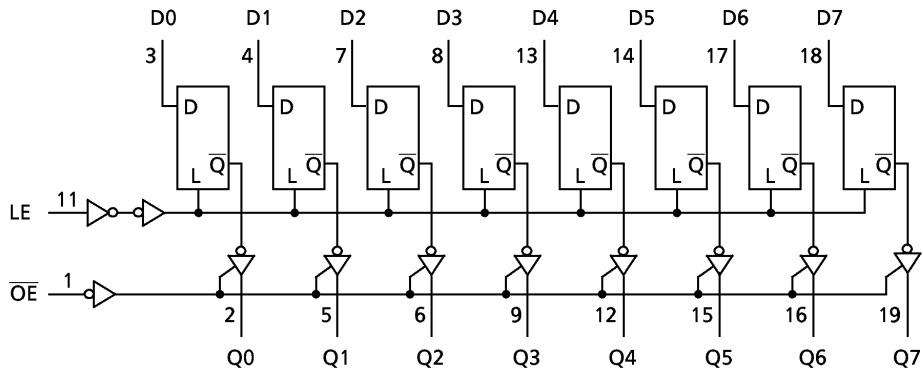
Q_n : Q outputs are latched at the time when the LE input is taken to a low logic level.

IEC LOGIC SYMBOL

961001EBA2

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SYSTEM DIAGRAM



ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V _{CC}	-0.5~7.0	V
DC Input Voltage	V _{IN}	-0.5~V _{CC} + 0.5	V
DC Output Voltage	V _{OUT}	-0.5~V _{CC} + 0.5	V
Input Diode Current	I _{IK}	± 20	mA
Output Diode Current	I _{OK}	± 50	mA
DC Output Current	I _{OUT}	± 50	mA
DC V _{CC} /Ground Current	I _{CC}	± 200	mA
Power Dissipation	P _D	500 (DIP)* / 180 (SOP/TSSOP)	mW
Storage Temperature	T _{stg}	-65~150	°C

*500mW in the range of Ta = -40°C~65°C. From Ta = 65°C to 85°C a derating factor of -10mW/°C should be applied up to 300mW.

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V _{CC}	2.0~5.5	V
Input Voltage	V _{IN}	0~V _{CC}	V
Output Voltage	V _{OUT}	0~V _{CC}	V
Operating Temperature	T _{opr}	-40~85	°C
Input Rise and Fall Time	dt / dV	0~ 100 (V _{CC} = 3.3 ± 0.3V) 0~ 20 (V _{CC} = 5 ± 0.5V)	ns / V

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DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	V _{CC} (V)	Ta = 25°C			Ta = -40~85°C		UNIT
				MIN.	TYP.	MAX.	MIN.	MAX.	
High - Level Input Voltage	V _{IH}		2.0 3.0 5.5	1.50 2.10 3.85	— — —	— — —	1.50 2.10 3.85	— — —	V
Low - Level Input Voltage	V _{IL}		2.0 3.0 5.5	— — —	— — —	0.50 0.90 1.65	— — —	0.50 0.90 1.65	V
High - Level Output Voltage	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -50μA	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5	— — —	1.9 2.9 4.4	V
			I _{OH} = -4mA I _{OH} = -24mA I _{OH} = -75mA*	3.0 4.5 5.5	2.58 3.94 —	— — —	— — —	2.48 3.80 3.85	
Low - Level Output Voltage	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 50μA	2.0 3.0 4.5	0.0 0.0 0.0	0.1 0.1 0.1	— — —	0.1 0.1 0.1	V
			I _{OL} = 12mA I _{OL} = 24mA I _{OL} = 75mA*	3.0 4.5 5.5	— — —	0.36 0.36 —	— — —	0.44 0.44 1.65	
3 - State Output Off - State Current	I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = V _{CC} or GND	5.5	—	—	± 0.5	—	± 5.0	μA
Input Leakage Current	I _{IN}	V _{IN} = V _{CC} or GND	5.5	—	—	± 0.1	—	± 1.0	
Quiescent Supply Current	I _{CC}	V _{IN} = V _{CC} or GND	5.5	—	—	8.0	—	80.0	

* : This spec indicates the capability of driving 50Ω transmission lines.

One output should be tested at a time for a 10ms maximum duration.

TIMING REQUIREMENTS (Input t_r = t_f = 3ns)

PARAMETER	SYMBOL	TEST CONDITION	Ta = 25°C		Ta = -40~85°C		UNIT
			V _{CC} (V)	LIMIT	LIMIT		
Minimum Pulse Width (LE)	t _W (H)		3.3 ± 0.3	7.0	7.0	ns	
			5.0 ± 0.5	5.0	5.0		
Minimum Set - up Time	t _s		3.3 ± 0.3	6.0	6.0	ns	
			5.0 ± 0.5	3.5	3.5		
Minimum Hold Time	t _h		3.3 ± 0.3	1.0	1.0	ns	
			5.0 ± 0.5	1.0	1.0		

AC ELECTRICAL CHARACTERISTICS ($C_L = 50\text{pF}$, $R_L = 500\Omega$, Input $t_r = t_f = 3\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	$V_{CC}(\text{V})$	$T_a = 25^\circ\text{C}$			$T_a = -40\sim85^\circ\text{C}$		UNIT	
				MIN.	TYP.	MAX.	MIN.	MAX.		
Propagation Delay Time (LE-Q)	t_{PLH} t_{PHL}		3.3 ± 0.3 5.0 ± 0.5	—	7.7 6.1	13.2 8.7	1.0 1.0	15.0 10.0	ns	
Propagation Delay Time (D-Q)	t_{PLH} t_{PHL}		3.3 ± 0.3 5.0 ± 0.5	—	7.6 5.8	12.9 8.3	1.0 1.0	14.7 9.5		
Output Enable Time	t_{pzL} t_{pzH}		3.3 ± 0.3 5.0 ± 0.5	—	7.6 6.1	12.9 8.7	1.0 1.0	14.7 10.0		
Output Disable Time	t_{pLZ} t_{pHZ}		3.3 ± 0.3 5.0 ± 0.5	—	7.0 5.4	11.0 7.5	1.0 1.0	12.5 8.5		
Input Capacitance	C_{IN}				—	5	10	—	10	pF
Output Capacitance	C_{OUT}				—	10	—	—	—	
Power Dissipation Capacitance	$C_{PD}(1)$				—	38	—	—	—	

Note(1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption.

Average operating current can be obtained by the equation :

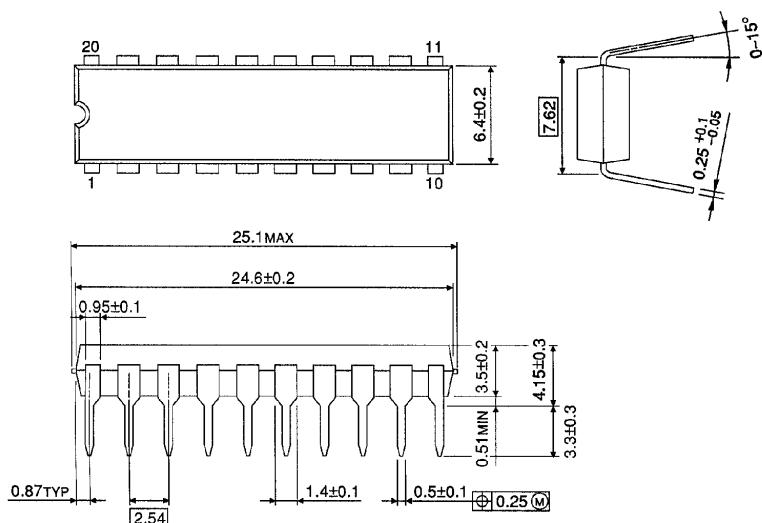
$$I_{CC(\text{opr})} = C_{PD} \cdot V_{CC} \cdot f_{IN} \cdot I_{CC} / 8(\text{per Latch})$$

And the total C_{PD} when n pcs. of Latch operate can be gained by the following equation :

$$C_{PD}(\text{total}) = 26 + 12 \cdot n$$

DIP 20PIN OUTLINE DRAWING (DIP20-P-300-2.54A)

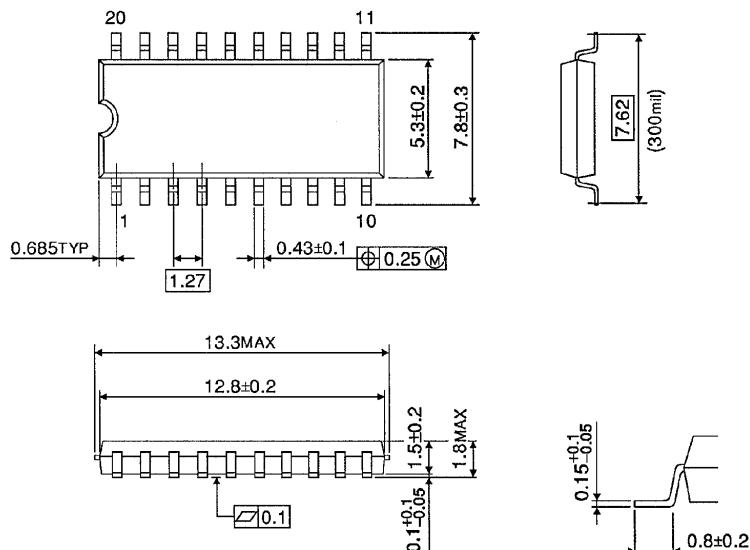
Unit in mm



Weight : 1.30g (Typ.)

SOP 20PIN (200mil BODY) OUTLINE DRAWING (SOP20-P-300-1.27)

Unit in mm

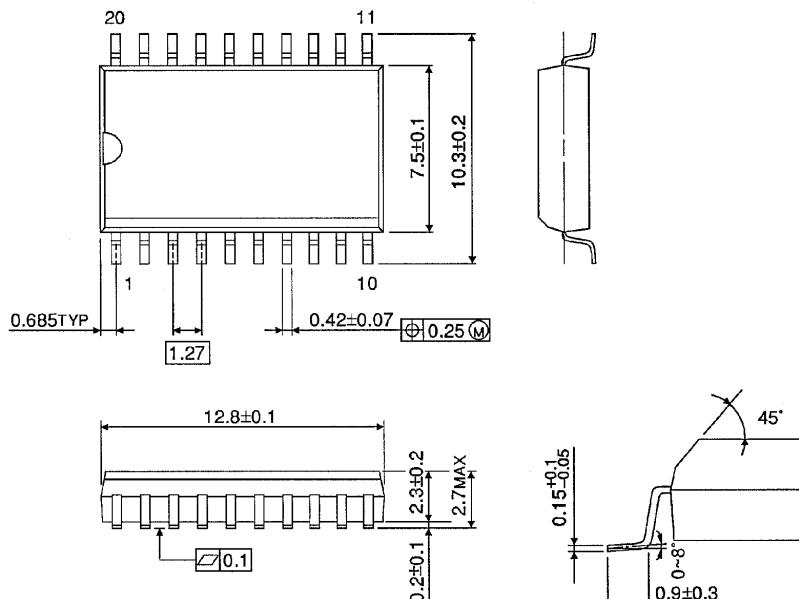


Weight : 0.22g (Typ.)

SOP 20PIN (300mil BODY) OUTLINE DRAWING (SOL20-P-300-1.27)

Unit in mm

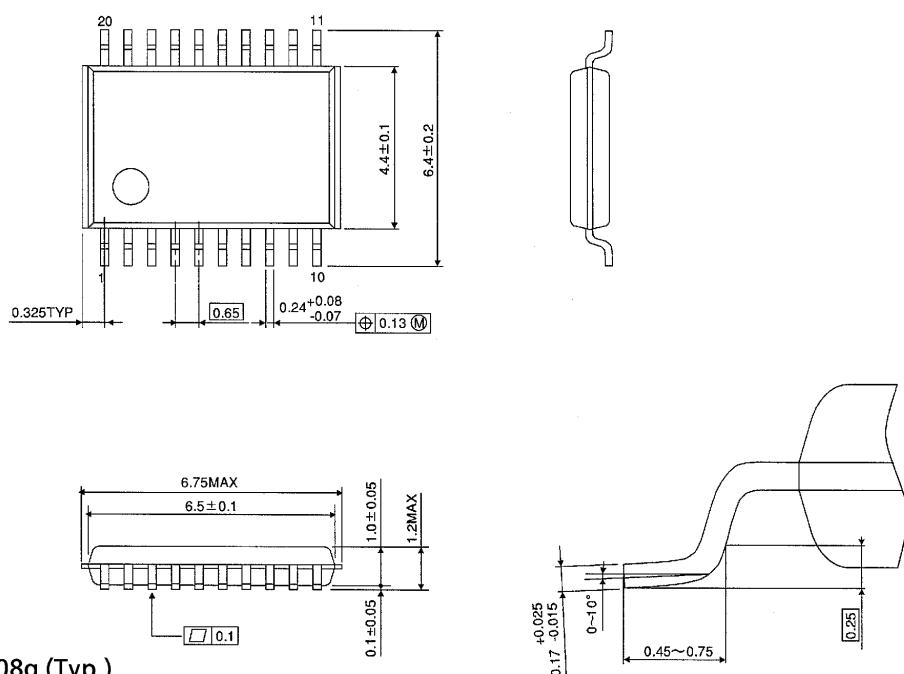
(Note) This package is not available in Japan.



Weight : 0.46g (Typ.)

TSSOP 20PIN OUTLINE DRAWING (TSSOP20-P-0044-0.65)

Unit in mm



Weight : 0.08g (Typ.)